Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	-	62	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	115	W
Static charact	teristics			'	'		
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C		-	11	13.6	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C		-	-	16.6	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12		-	13	15	mΩ
Dynamic char	racteristics			'	'		
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 44 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 9$		-	20	-	nC



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)} S	non-repetitive drain- source avalanche energy	I_D = 62 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	211	mJ

^[1] Current is limited by power dissipation chip rating.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D L
2	D	drain		
3	S	source	\\\\	G UNA
mb	D	mounting base; connected to drain	1 3 DPAK (SOT428)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9215-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

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Limiting values 7.

Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	55	V
V_{GS}	gate-source voltage			-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	115	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	62	Α
			[2]	-	55	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[1]	-	44	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3		-	248	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
Is	source current	T _{mb} = 25 °C	[2]	-	55	Α
			[1]	-	62	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	248	Α
Avalanche	ruggedness			'		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 62 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	211	mJ

^[1] Current is limited by power dissipation chip rating.[2] Continious current is limited by bond wires.

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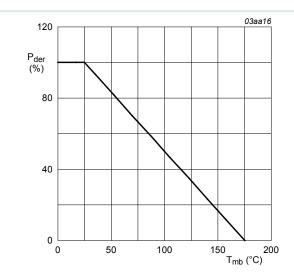


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times \textbf{100 \%}$$

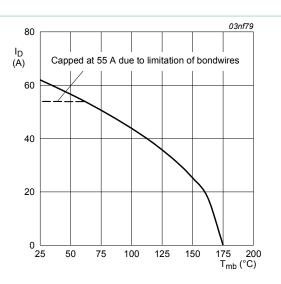


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

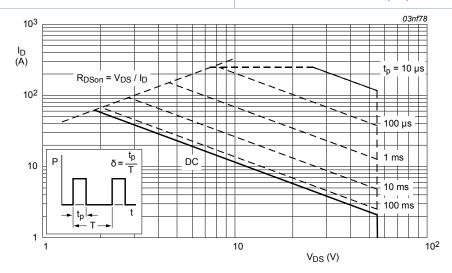


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C; I_{DM}$ is single pulse

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	1.3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W

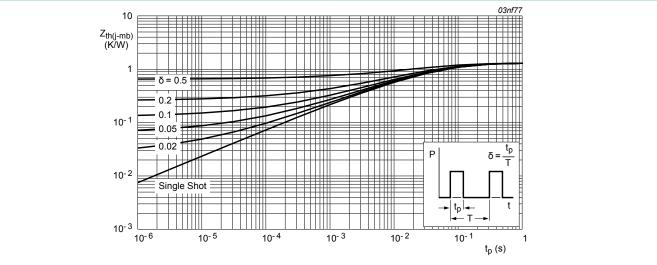


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	55	-	-	V
bre	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.3	٧
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10	1	1.5	2	٧
I _{DSS} drain leaka	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	11	13.6	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	16.6	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	30	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11; Fig. 12	-	13	15	mΩ
Dynamic o	characteristics		'			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 44 V; V _{GS} = 5 V;	-	48	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 9</u>	-	6	-	nC
Q_GD	gate-drain charge		-	20	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	2190	2916	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>	-	380	450	pF
C _{rss}	reverse transfer capacitance		-	250	344	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 5 V;	-	19	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	161	-	ns
t _{d(off)}	turn-off delay time		-	138	-	ns
t _f	fall time		-	165	-	ns
L _D	internal drain inductance	measured from drain to centre of die	-	2.5	-	nH

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
L _S	internal source inductance	measured from source lead to source bond pad		-	7.5	-	nH
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 14$		-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$		-	51	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$		-	102	-	nC

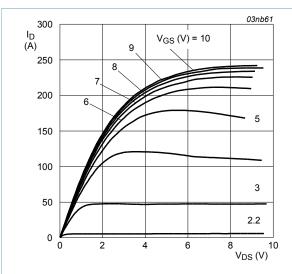


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25^{\circ}C$$

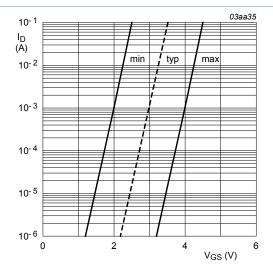


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25\,^{\circ}C; V_{DS} = 5V$$

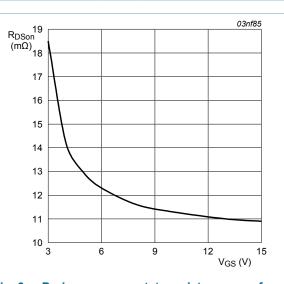


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

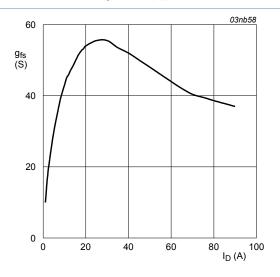


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j=25^{\circ}C; V_{DS}=25V$$

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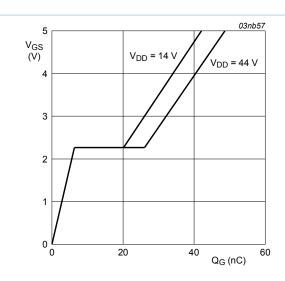


Fig. 9. Gate-source voltage as a function of turn-on gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

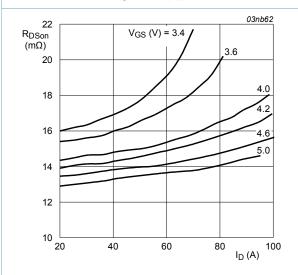


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

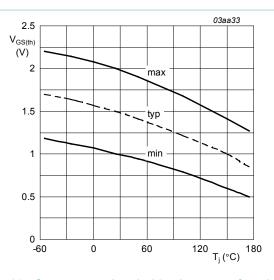


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

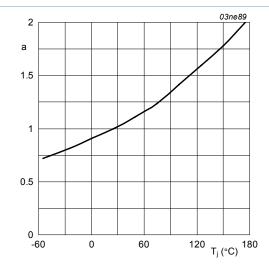


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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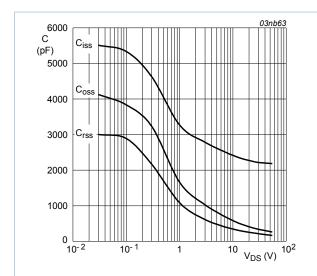
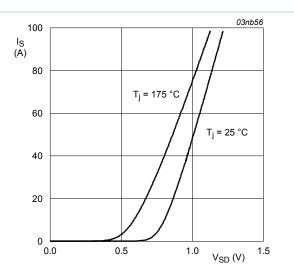


Fig. 13. Input, output and reverse transfer capacitances Fig. 14. Reverse diode current; typical value as a function of drain-source voltage; typical values

$$V_{GS}=0V; f=1MHz$$



$$V_{GS} = 0V$$

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10. Package outline

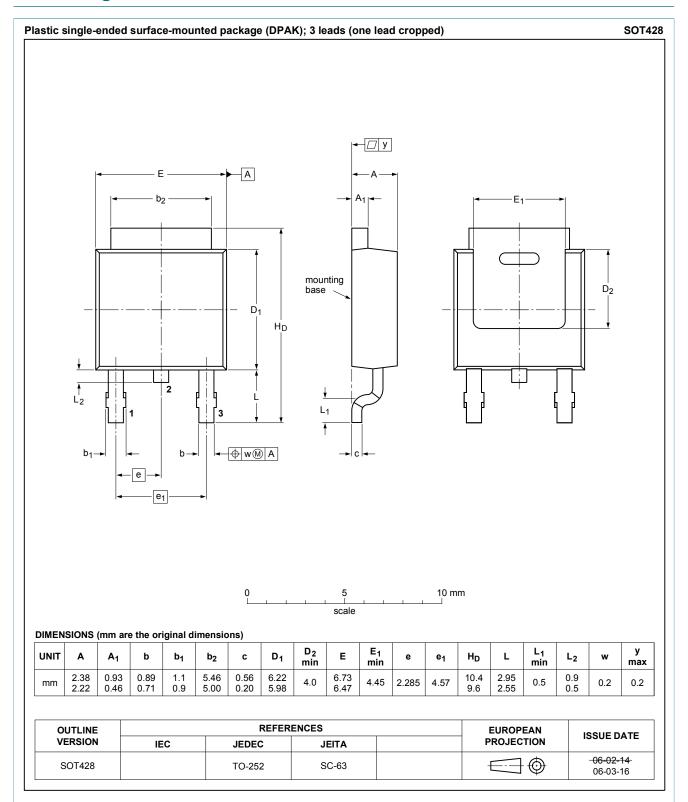


Fig. 15. Package outline DPAK (SOT428)

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